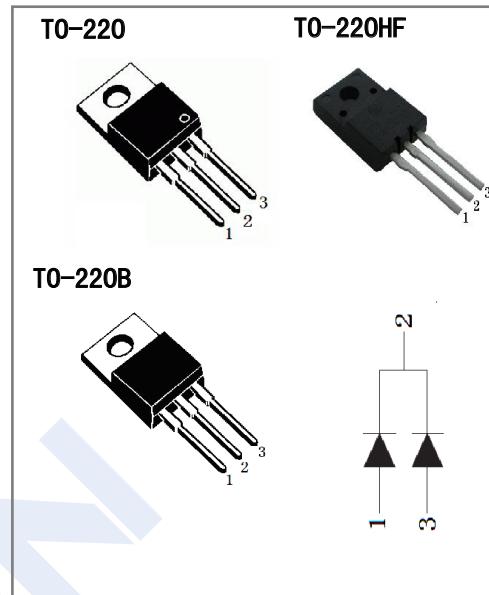


**Schottky Diodes****MBR20100U****■ Features**

- Common cathode structure
- Low power loss, high efficiency
- High Operating Junction Temperature
- Guard ring for overvoltage protection, High reliability

**■ Absolute Maximum Ratings Ta = 25°C**

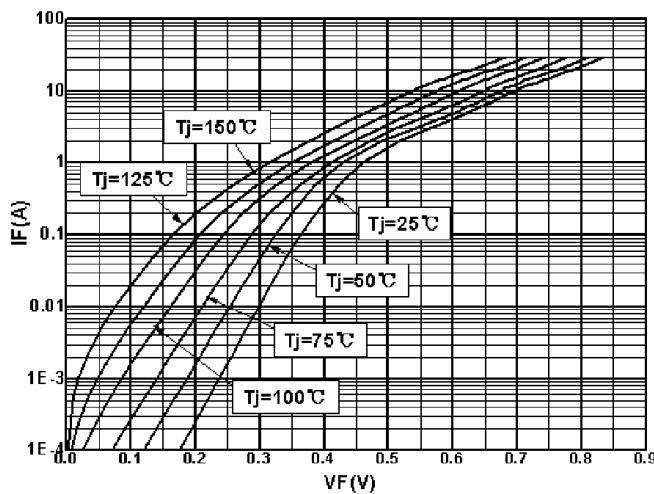
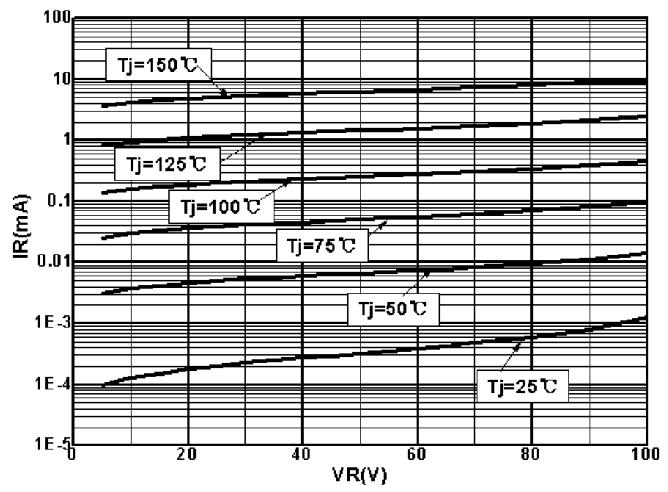
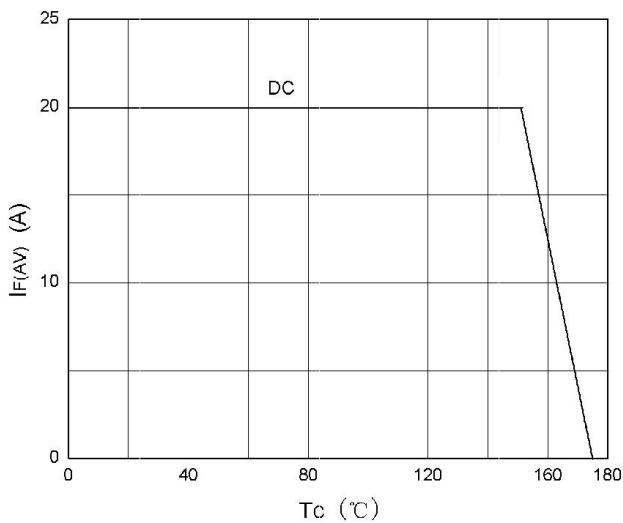
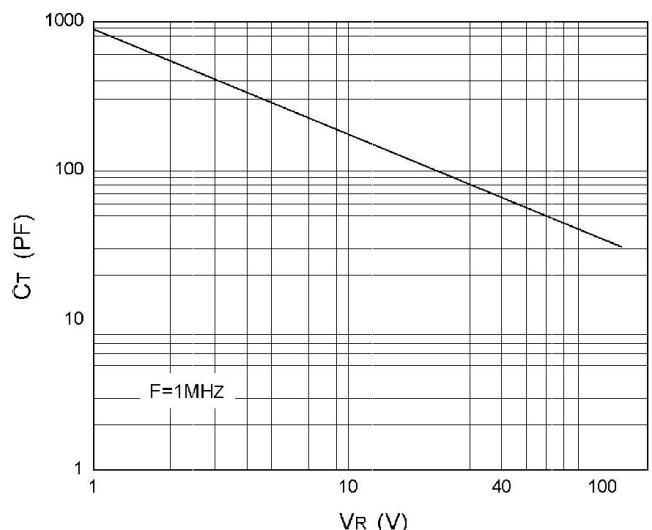
Parameter	Symbol	Rating	Unit
Reverse Voltage	V <sub>RM</sub>	100	V
DC blocking voltage	V <sub>D<sub>C</sub></sub>	100	
Average Forward Current (T <sub>c</sub> =150°C TO-220) (T <sub>c</sub> =125°C TO 220HF)	I <sub>FAV</sub>	20 10	A
Peak Forward Surge Current	I <sub>FSM</sub>	200	
Thermal Resistance Junction to Case TO-220 TO-220B TO-220HF	R <sub>θJC</sub>	1.9 1.9 2.5	°C/W
Junction Temperature	T <sub>J</sub>	175	
Storage Temperature range	T <sub>stg</sub>	-40 to 150	°C

**■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 A T <sub>J</sub> =25°C		0.69	0.73	V
		I <sub>F</sub> = 10 A T <sub>J</sub> =125°C		0.57	0.62	
		I <sub>F</sub> = 15 A T <sub>J</sub> =25°C		0.75	0.8	
		I <sub>F</sub> = 15 A T <sub>J</sub> =125°C		0.62	0.7	
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> = V <sub>RRM</sub> T <sub>J</sub> =25°C			20	uA
		V <sub>R</sub> = V <sub>RRM</sub> T <sub>J</sub> =125°C			5	mA

**Schottky Diodes****MBR20100U**

## ■ Typical Characteristics

 $I_F$  vs  $V_F$  $I_R$  vs  $V_R$  $|I_{F(AV)}$  vs  $T_C$  $C_T$  vs  $V_R$ 

## Schottky Diodes

## MBR20100U

## ■ Package size chart

